

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The ASI VHB10-28S is Designed for

FEATURES:

-
-
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	1.0 A
V_{CB0}	65 V
V_{CEO}	35 V
V_{CES}	65 V
V_{EBO}	4.0 V
P_{DISS}	13.0 W
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	5.5 °C/W

PACKAGE STYLE .380 4L STUD

DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B	.980 / 24.89	
C	.370 / 9.40	.385 / 9.78
D	.004 / 0.10	.007 / 0.18
E	.320 / 8.13	.330 / 8.38
F	.100 / 2.54	.130 / 3.30
G	.450 / 11.43	.490 / 12.45
H	.090 / 2.29	.100 / 2.54
I	.155 / 3.94	.175 / 4.45
J		.750 / 19.05

ORDER CODE: ASI10723

CHARACTERISTICS $T_C = 25\text{ }^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CB0}	I _C = 200 mA	65			V
BV_{CES}	I _C = 200 mA	65			V
BV_{CEO}	I _C = 200 mA	35			V
BV_{EBO}	I _E = 10 mA	4.0			V
I_{CB0}	V _{CB} = 30 V			1.0	mA
h_{FE}	V _{CE} = 5.0 V I _C = 200 mA	5.0		---	---
C_{ob}	V _{CB} = 28 V f = 1.0 MHz			15	pF
P_G	V _{CC} = 28 V P _{OUT} = 10 W f = 175 MHz	10			dB
η_C			60		%